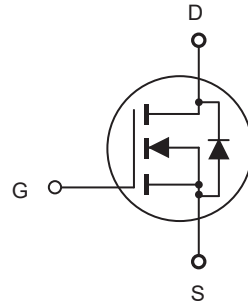


## N-Channel Enhancement Mode Field Effect Transistor

### FEATURES

- 200V, 15A,  $R_{DS(ON)} = 150m\Omega$  @  $V_{GS} = 10V$ .
- Super high dense cell design for extremely low  $R_{DS(ON)}$ .
- High power and current handling capability.
- Pb-free lead plating ; RoHS compliant.
- Halogen Free.
- TO-251 & TO-252 package.



### ABSOLUTE MAXIMUM RATINGS $T_C = 25^\circ C$ unless otherwise noted

Parameter	Symbol	Limit	Units
Drain-Source Voltage	$V_{DS}$	200	V
Gate-Source Voltage	$V_{GS}$	$\pm 30$	V
Drain Current-Continuous @ $T_C = 25^\circ C$ @ $T_C = 100^\circ C$	$I_D$	15	A
		9	A
Drain Current-Pulsed <sup>a</sup>	$I_{DM}$	60	A
Maximum Power Dissipation @ $T_C = 25^\circ C$ - Derate above $25^\circ C$	$P_D$	69.4	W
		0.55	W/ $^\circ C$
Single Pulsed Avalanche Energy <sup>d</sup>	$E_{AS}$	242	mJ
Single Pulsed Avalanche Current <sup>d</sup>	$I_{AS}$	22	A
Operating and Store Temperature Range	$T_J, T_{stg}$	-55 to 150	$^\circ C$

### Thermal Characteristics

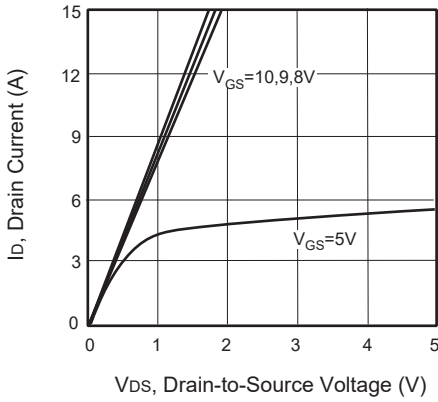
Parameter	Symbol	Limit	Units
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.8	$^\circ C/W$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	50	$^\circ C/W$



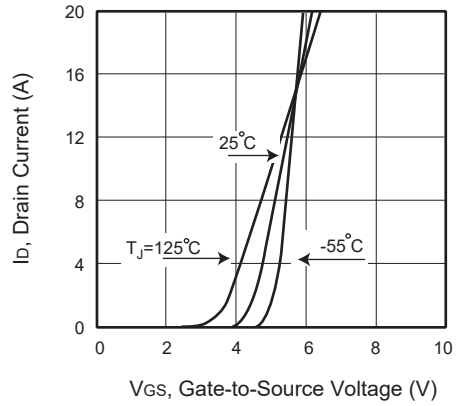
# CEDF640A/CEUF640A

## Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

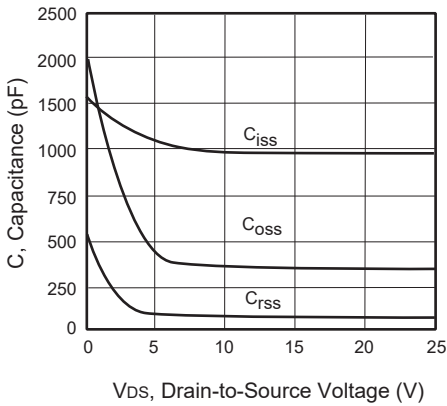
Parameter	Symbol	Test Condition	Min	Typ	Max	Units
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	200			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 200V, V_{GS} = 0V$			1	$\mu A$
Gate Body Leakage Current, Forward	$I_{GSSF}$	$V_{GS} = 30V, V_{DS} = 0V$			100	nA
Gate Body Leakage Current, Reverse	$I_{GSSR}$	$V_{GS} = -30V, V_{DS} = 0V$			-100	nA
<b>On Characteristics<sup>b</sup></b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS} = V_{DS}, I_D = 250\mu A$	2		4	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 10A$		114	150	m $\Omega$
<b>Dynamic Characteristics<sup>c</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 25V, V_{GS} = 0V, f = 1.0\text{ MHz}$		985		pF
Output Capacitance	$C_{oss}$			335		pF
Reverse Transfer Capacitance	$C_{rss}$			70		pF
<b>Switching Characteristics<sup>c</sup></b>						
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 100V, I_D = 11A, V_{GS} = 10V, R_{GEN} = 9.1\Omega$		16		ns
Turn-On Rise Time	$t_r$			5		ns
Turn-Off Delay Time	$t_{d(off)}$			33		ns
Turn-Off Fall Time	$t_f$			10		ns
Total Gate Charge	$Q_g$	$V_{DS} = 160V, I_D = 15A, V_{GS} = 10V$		23		nC
Gate-Source Charge	$Q_{gs}$			4		nC
Gate-Drain Charge	$Q_{gd}$			12		nC
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
Drain-Source Diode Forward Current	$I_S$				15	A
Drain-Source Diode Forward Voltage <sup>b</sup>	$V_{SD}$	$V_{GS} = 0V, I_S = 10A$			1.5	V
<b>Notes :</b> a. Repetitive Rating : Pulse width limited by maximum junction temperature. b. Pulse Test : Pulse Width $\leq 300\mu s$ , Duty Cycle $\leq 2\%$ . c. Guaranteed by design, not subject to production testing. d. L = 1mH, $I_{AS} = 22A, V_{DD} = 25V, R_G = 25\Omega$ , Starting $T_J = 25^\circ\text{C}$ .						



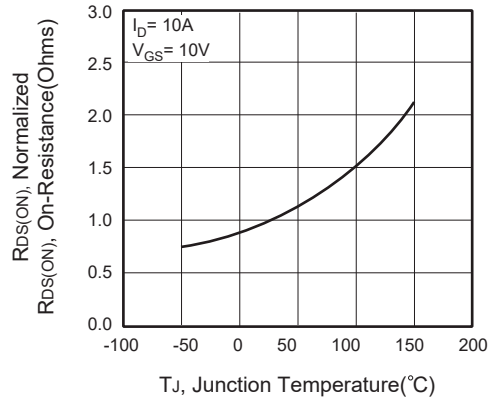
**Figure 1. Output Characteristics**



**Figure 2. Transfer Characteristics**



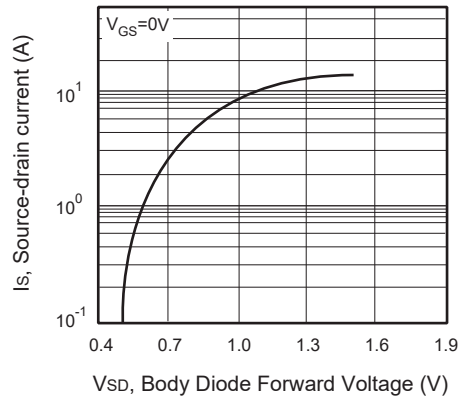
**Figure 3. Capacitance**



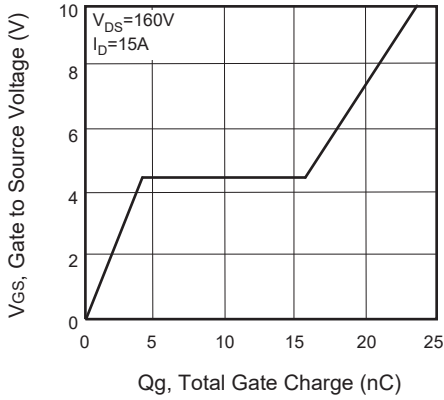
**Figure 4. On-Resistance Variation with Temperature**



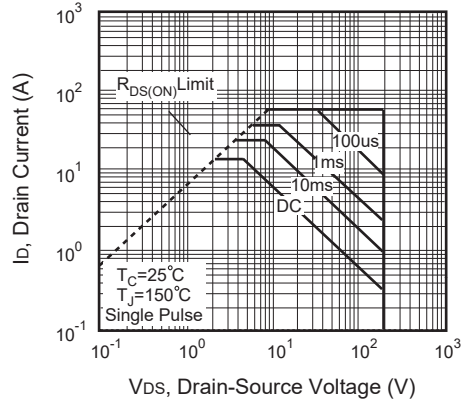
**Figure 5. Gate Threshold Variation with Temperature**



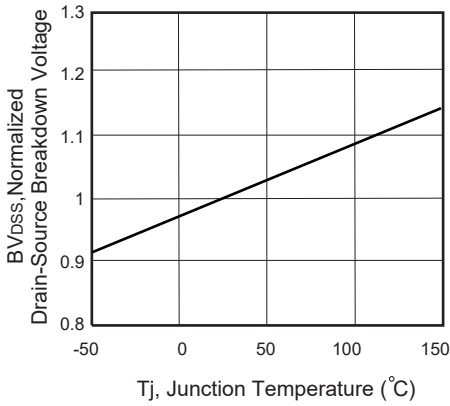
**Figure 6. Body Diode Forward Voltage Variation with Source Current**



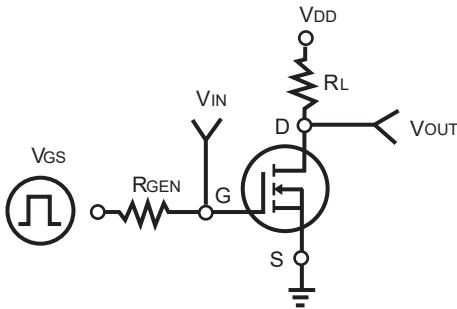
**Figure 7. Gate Charge**



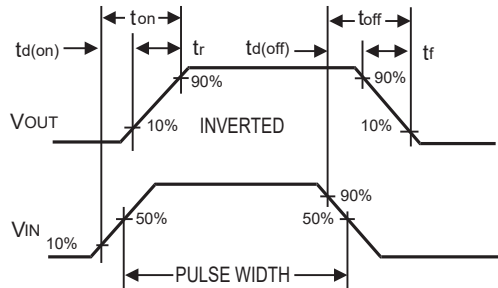
**Figure 8. Maximum Safe Operating Area**



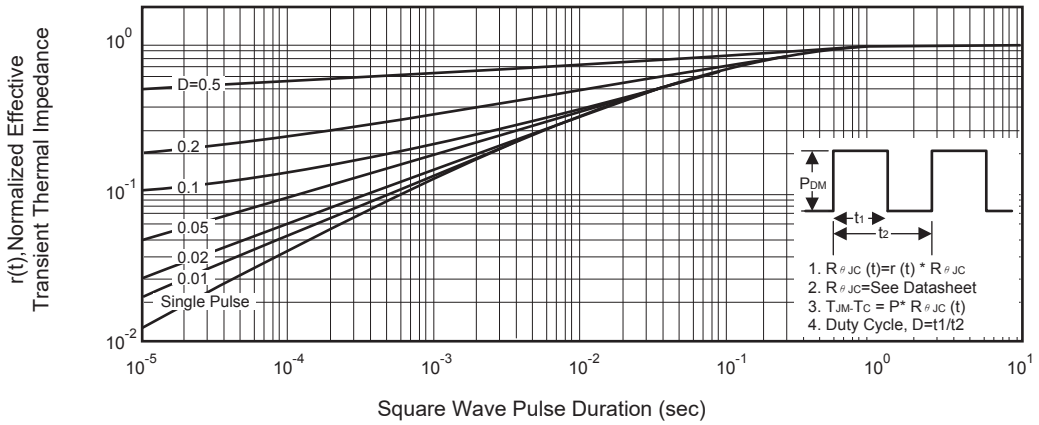
**Figure 9. Breakdown Voltage Variation VS Temperature**



**Figure 10. Switching Test Circuit**



**Figure 11. Switching Waveforms**



**Figure 12. Normalized Thermal Transient Impedance Curve**